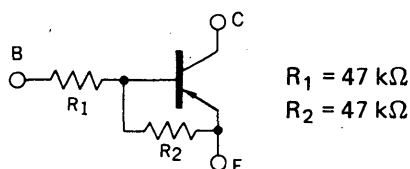


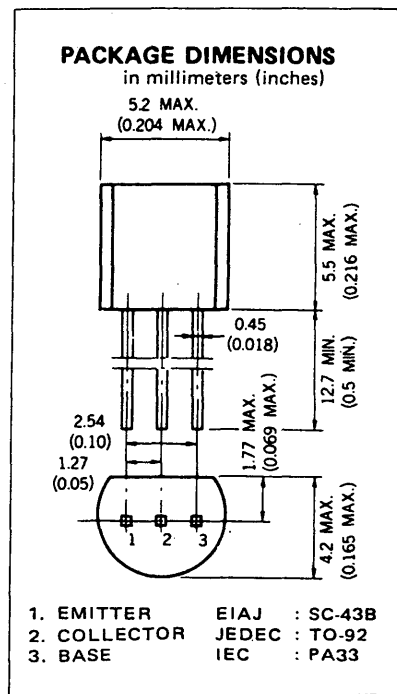
DESCRIPTION The AN1L4M is designed for use in medium speed switching circuit.

FEATURE • Bias resistors built-in type PNP transistor equivalent circuit.



ABSOLUTE MAXIMUM RATINGS

Maximum Temperatures	
Storage Temperature	-55 to +150 °C
Junction Temperature	150 °C Maximum
Maximum Power Dissipation ($T_a = 25 \text{ }^\circ\text{C}$)	
Total Power Dissipation	300 mW
Maximum Voltages and Currents ($T_a = 25 \text{ }^\circ\text{C}$)	
V_{CBO} Collector to Base Voltage	-60 V
V_{CEO} Collector to Emitter Voltage	-50 V
V_{EBO} Emitter to Base Voltage	-10 V
$I_C(\text{DC})$ Collector Current (DC)	-100 mA
$I_C(\text{pulse})$ Collector Current (pulse)	-200 mA



ELECTRICAL CHARACTERISTICS ($T_a = 25 \text{ }^\circ\text{C}$)

SYMBOL	CHARACTERISTIC	MIN.	TYP.	MAX.	UNIT	TEST CONDITIONS
R_1	Input Resistance	32.9	47.0	61.1	k Ω	
R_1/R_2	Resistors Ratio	0.9	1.0	1.1	-	
V_{iL}	Low Level Input Voltage	-1.5	-1.17		V	$V_{CE} = -5.0 \text{ V}, I_C = -100 \mu\text{A}$
V_{iH}	Hi Level Input Voltage	-5.0	-2.4		V	$V_{CE} = -0.2 \text{ V}, I_C = -5.0 \text{ mA}$
t_{on}	Turn on Time		0.5	1.0	μs	$V_{CC} = -5.0 \text{ V}, R_L = 1.0 \text{ k}\Omega$ $V_{in} = -5.0 \text{ V}$ $PW = 2 \mu\text{s}, \text{Duty Cycle} \leq 2 \%$
t_{stg}	Storage Time		0.8	3.0	μs	
t_{off}	Turn off Time		1.4	4.0	μs	
h_{FE1}	DC Current Gain	85	135	340	-	$V_{CE} = -5.0 \text{ V}, I_C = -5.0 \text{ mA}$
h_{FE2}	DC Current Gain	95	180		-	$V_{CE} = -5.0 \text{ V}, I_C = -5.0 \text{ mA}$
$V_{CE(\text{sat})}$	Collector Saturation Voltage		-0.05	-0.2	V	$I_C = -5.0 \text{ mA}, I_B = -0.25 \text{ mA}$
I_{CBO}	Collector Cutoff Current			-0.1	μA	$V_{CB} = -50 \text{ V}, I_E = 0$

TYPICAL CHARACTERISTICS ($T_a = 25^\circ\text{C}$)

